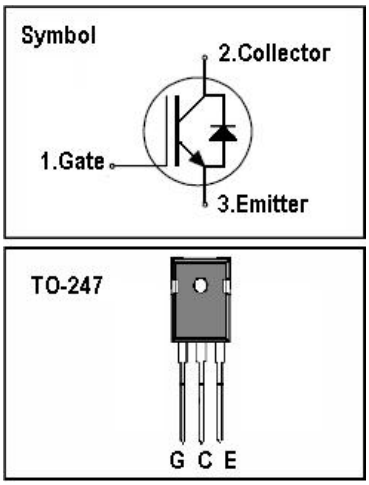
LGEGW60N65SEU

650V/60A Trehch Field Stop IGBT



Features

- 650V 60A,$V_{CE(sat)(typ.)}$ = 2.3 V@60A
- Field Stop IGBT Technology.
- 10μs Short Circuit Capability.
- Square RBSOA.
- Positive VCE (on) Temperature Coefficient.

Benefits

- High Efficiency for Welding, Inductive heating, UPS and other high frequency application
- Rugged Performance
- Excellent Current Sharing in Parallel Operation

Absolute Maxinmun Ratings

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate-Emitter Voltage	±30	V
I_C	Continuous Collector Current (T_C=25 ℃)	120	A
	Continuous Collector Current (T_C=100℃)	60	A
I_{CM}	Pulsed Collector Current (Note 1)	240	A
I_F	Diode Continuous Forward Current (T_C=100 ℃)	60	A
I_{FM}	Diode Maximum Forward Current (Note 1)	240	A
t_{sc}	Short Circuit Withstand Time	10	us
Isc	Short Circuit Current	270	A
P_D	Maximum Power Dissipation (T_C=25 ℃)	378	W
P_D	Maximum Power Dissipation (T_C=100℃)	151	W
T_J	Operating Junction Temperature Range	-55 to +150	℃
T_{STG}	Storage Temperature Range	-55 to +150	℃

Thermal Characteristics

Symbol	Parameter	Max.	Units
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to case for IGBT	0.33	℃/ W
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to case for Diode	0.65	℃/ W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	80	℃/ W

Electrical Characteristics (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{CES}	Collector-Emitter Breakdown Voltage	V_{GE}= 0V, I_C= 250uA	650	-	-	V
I_{CES}	Collector-Emitter Leakage Current	V_{CE}= 650V, V_{GE}= 0V	-	-	250	uA
I_{GES}	Gate Leakage Current, Forward	V_{GE}=30V, V_{CE}= 0V	-	-	100	nA
	Gate Leakage Current, Reverse	V_{GE}= -30V, V_{CE}= 0V	-	-	-100	nA
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE}= V_{CE}, I_C= 250uA	4.0	-	5.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE}=15V, I_C= 40A	-	2.3		V
Q_g	Total Gate Charge	V_{CC}=480V V_{GE}=15V I_C=60A	-	210		nC
Q_{ge}	Gate-Emitter Charge		-	28		nC
Q_{gc}	Gate-Collector Charge		-	115		nC
$t_{d(on)}$	Turn-on Delay Time	V_{CC}=400V V_{GE}=15V I_C=60A R_G=10Ω Inductive Load T_C=25℃	-	31	-	ns
t_r	Turn-on Rise Time		-	82	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	196	-	ns
t_f	Turn-off Fall Time		-	60	-	ns
Eon	Turn-on Switching Loss		-	2.55	-	mJ
Eoff	Turn-off Switching Loss		-	1.75	-	mJ
C_{ies}	Input Capacitance	V_{CE}=25V V_{GE}=0V f = 1MHz	-	2020	-	pF
C_{oes}	Output Capacitance		-	280	-	pF
C_{res}	Reverse Transfer Capacitance		-	130	-	pF
R_{Gint}	Integrated gate resistor	f=1MHz;Vpp=1V		1.55		Ω

Electrical Characteristics of Diode(T_C=25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	I_F=60A	-	1.35		V
t_{rr}	Diode Reverse Recovery Time	V_{CE} = 400V I_F= 60A dI_F/dt = 500A/us	-	150		ns
I_{rrm}	Diode peak Reverse Recovery Current		-	22		A
Q_{rr}	Diode Reverse Recovery Charge		-	1320		nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

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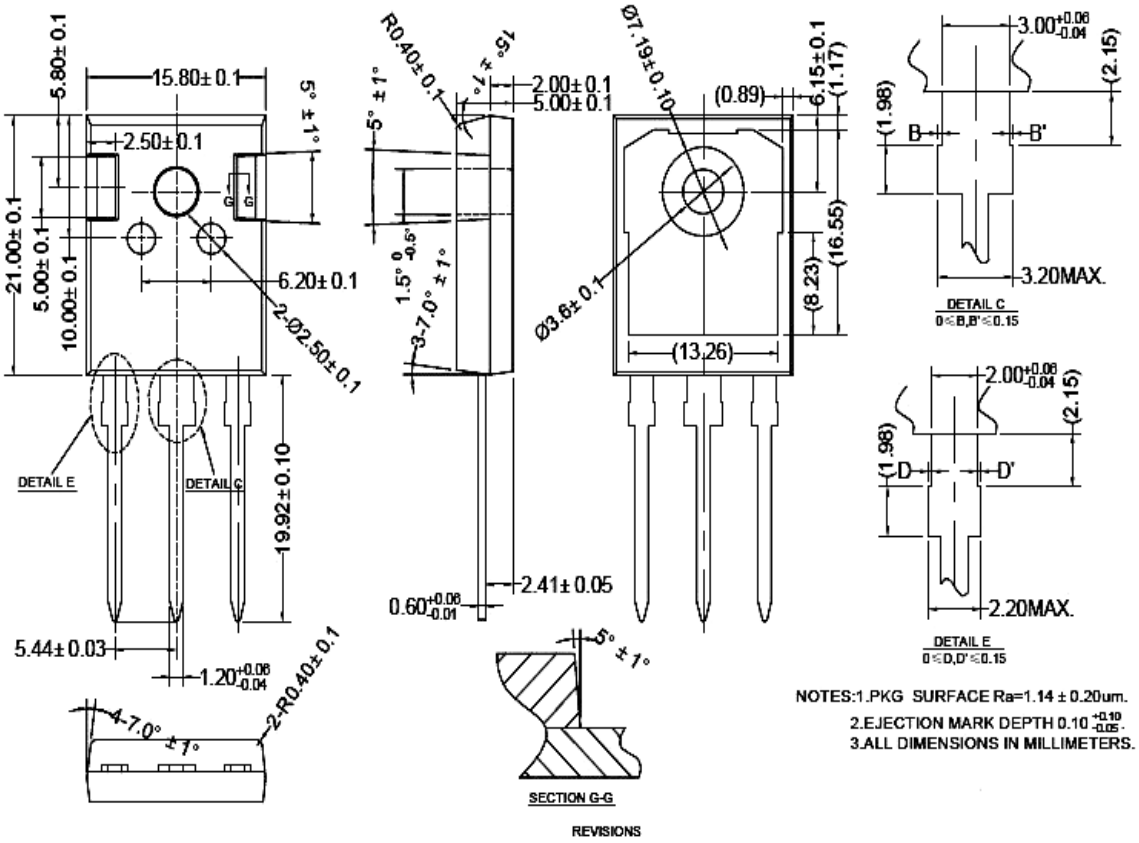

公差标注	公差值	表面粗糙度
0	±0.2	Ra3.2~6.3
0.0	±0.1	Ra1.6~3.2
0.00	±0.01	Ra0.8~1.6
0.000	±0.005	Ra0.4~0.8
0.0000	±0.002	Ra0.2~0.4

0≤D,D'≤0.15
NOTES:1.PKG SURFACE Ra=1.14 ± 0.20um.
2.EJECTION MARK DEPTH 0.10 +0.10 -0.05
3.ALL DIMENSIONS IN MILLIMETERS.